

HIGH AND LOW SIDE DRIVER

Features

- Floating channel designed for bootstrap operation Fully operational to +600V Tolerant to negative transient voltage dV/dt immune
- Gate drive supply range from 10 to 20V
- Undervoltage lockout for both channels
- 3.3V, 5V and 15V input logic compatible
- Cross-conduction prevention logic
- Matched propagation delay for both channels
- High side output in phase with HIN input
- Low side output out of phase with LIN input
- Logic and power ground +/- 5V offset.
- Internal 500ns dead-time, and programmable up to 5us with one external R_{DT} resistor (IR21084)
- Lower di/dt gate driver for better noise immunity

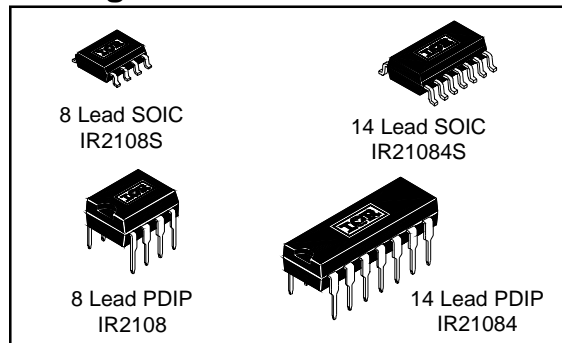
Description

The IR2108/IR21084 are high voltage, high speed power MOSFET and IGBT drivers with dependent high and low side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. The logic input is compatible with standard CMOS or LSTTL output, down to 3.3V logic. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration which operates up to 600 volts.

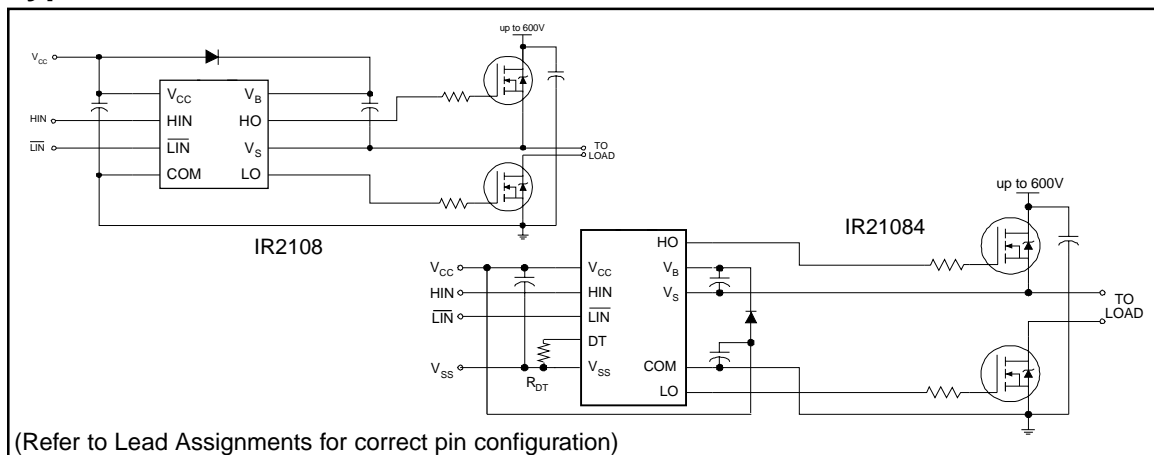
Product Summary

V _{OFFSET}	600V max.
I _{O+/-}	120 mA / 250 mA
V _{OUT}	10 - 20V
t _{on/off} (typ.)	180 ns
Deadtime (typ.)	500 ns
	(programmable up to 5us for IR21084)

Packages



Typical Connection



IR2108/IR21084 (S)

Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Min.	Max.	Units	
V _B	High side floating absolute voltage	-0.3	625	V	
V _S	High side floating supply offset voltage	V _B - 25	V _B + 0.3		
V _{HO}	High side floating output voltage	V _S - 0.3	V _B + 0.3		
V _{CC}	Low side and logic fixed supply voltage	-0.3	25		
V _{LO}	Low side output voltage	-0.3	V _{CC} + 0.3		
DT	Programmable dead-time pin voltage (IR21084 only)	V _{SS} - 0.3	V _{CC} + 0.3		
V _{IN}	Logic input voltage (HIN & LIN)	V _{SS} - 0.3	V _{CC} + 0.3		
V _{SS}	Logic ground (IR21084 only)	V _{CC} - 25	V _{CC} + 0.3		
dV _S /dt	Allowable offset supply voltage transient	—	50	V/ns	
P _D	Package power dissipation @ T _A ≤ +25°C	(8 lead PDIP)	—	1.0	W
		(8 lead SOIC)	—	0.625	
		(14 lead PDIP)	—	1.6	
		(14 lead SOIC)	—	1.0	
R _{thJA}	Thermal resistance, junction to ambient	(8 lead PDIP)	—	125	°C/W
		(8 lead SOIC)	—	200	
		(14 lead PDIP)	—	75	
		(14 lead SOIC)	—	120	
T _J	Junction temperature	—	150	°C	
T _S	Storage temperature	-50	150		
T _L	Lead temperature (soldering, 10 seconds)	—	300		

Recommended Operating Conditions

The Input/Output logic timing diagram is shown in figure 1. For proper operation the device should be used within the recommended conditions. The V_S and V_{SS} offset rating are tested with all supplies biased at 15V differential.

Symbol	Definition	Min.	Max.	Units
V _B	High side floating supply absolute voltage	V _S + 10	V _S + 20	V
V _S	High side floating supply offset voltage	Note 1	600	
V _{HO}	High side floating output voltage	V _S	V _B	
V _{CC}	Low side and logic fixed supply voltage	10	20	
V _{LO}	Low side output voltage	0	V _{CC}	
V _{IN}	Logic input voltage (HIN & LIN)	V _{SS}	V _{CC}	
DT	Programmable dead-time pin voltage (IR21084 only)	V _{SS}	V _{CC}	
V _{SS}	Logic ground (IR21084 only)	-5	5	°C
T _A	Ambient temperature	-40	125	

Note 1: Logic operational for V_S of -5 to +600V. Logic state held for V_S of -5V to -V_{BS}.

Dynamic Electrical Characteristics

V_{BIAS} (V_{CC}, V_{BS}) = 15V, V_{SS} = COM, C_L = 1000 pF, T_A = 25°C, DT = V_{SS} unless otherwise specified.

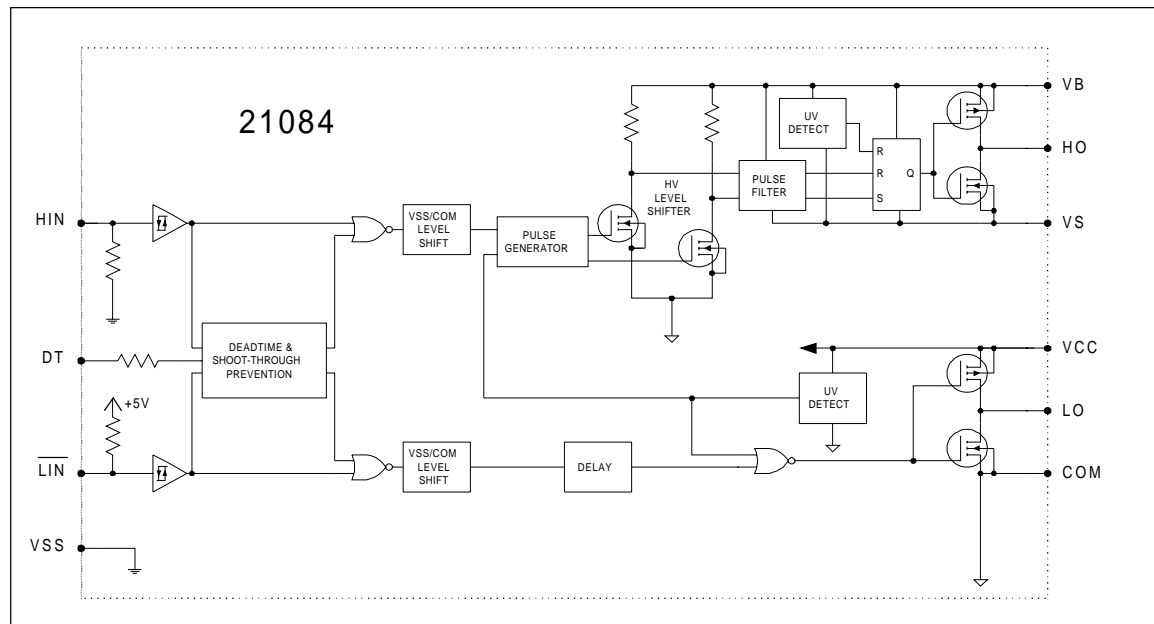
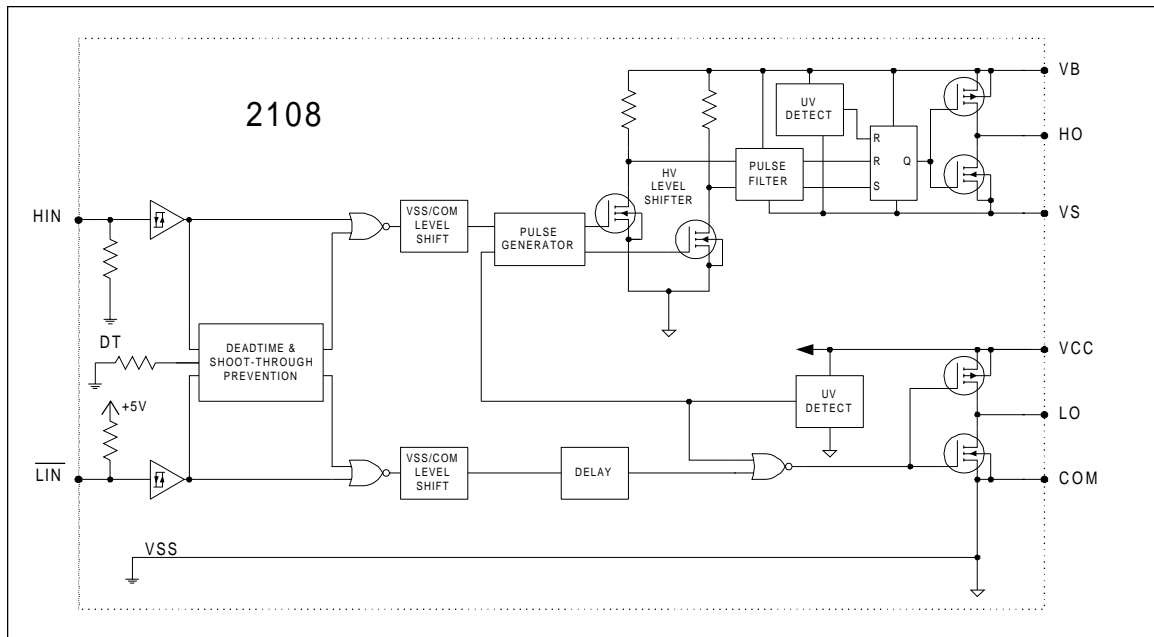
Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
t _{on}	Turn-on propagation delay	—	180	270	nsec	V _S = 0V
t _{off}	Turn-off propagation delay	—	170	250		V _S = 0V or 600V
MT	Delay matching, HS & LS turn-on/off	—	0	50		
t _r	Turn-on rise time	—	150	220		V _S = 0V
t _f	Turn-off fall time	—	50	80		V _S = 0V
DT	Deadtime: LO turn-off to HO turn-on(DT _{LO-HO})	380	500	620		usec
	HO turn-off to LO turn-on (DT _{HO-LO})	4	5	6	RDT = 200k (IR21084)	
MDT	Deadtime matching = DT _{LO-HO} - DT _{HO-LO}	—	0	60	nsec	RDT=0
		—	0	600		RDT = 200k (IR21084)

Static Electrical Characteristics

V_{BIAS} (V_{CC}, V_{BS}) = 15V, V_{SS} = COM, DT= V_{SS} and T_A = 25°C unless otherwise specified. The V_{IL}, V_{IH} and I_{IN} parameters are referenced to V_{SS}/COM and are applicable to the respective input leads: H_{IN} and L_{IN}. The V_O, I_O and R_{on} parameters are referenced to COM and are applicable to the respective output leads: HO and LO.

Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
V _{IH}	Logic "1" input voltage for H _{IN} & logic "0" for L _{IN}	2.7	—	—	V	V _{CC} = 10V to 20V
V _{IL}	Logic "0" input voltage for H _{IN} & logic "1" for L _{IN}	—	—	0.8		V _{CC} = 10V to 20V
V _{OH}	High level output voltage, V _{BIAS} - V _O	—	0.8	1.4		I _O = 20 mA
V _{OL}	Low level output voltage, V _O	—	0.3	0.6		I _O = 20 mA
I _{LK}	Offset supply leakage current	—	—	50	μA	V _B = V _S = 600V
I _{QBS}	Quiescent V _{BS} supply current	20	60	150	μA	V _{IN} = 0V or 5V
I _{QCC}	Quiescent V _{CC} supply current	0.4	1.0	1.6	mA	V _{IN} = 0V or 5V RDT=0
I _{IN+}	Logic "1" input bias current	—	5	20	μA	H _{IN} = 5V, L _{IN} = 0V
I _{IN-}	Logic "0" input bias current	—	1	2		H _{IN} = 0V, L _{IN} = 5V
V _{CCUV+} V _{BSUV+}	V _{CC} and V _{BS} supply undervoltage positive going threshold	8.0	8.9	9.8	V	
V _{CCUV-} V _{BSUV-}	V _{CC} and V _{BS} supply undervoltage negative going threshold	7.4	8.2	9.0		
V _{CCUVH} V _{BSUVH}	Hysteresis	0.3	0.7	—		
I _{O+}	Output high short circuit pulsed current	120	200	—	mA	V _O = 0V, PW ≤ 10 μs
I _{O-}	Output low short circuit pulsed current	250	350	—		V _O = 15V, PW ≤ 10 μs

Functional Block Diagram



Lead Definitions

Symbol	Description
HIN	Logic input for high side gate driver output (HO), in phase (referenced to COM for IR2108 and VSS for IR21084)
LIN	Logic input for low side gate driver output (LO), out of phase (referenced to COM for IR2108 and VSS for IR21084)
DT	Programmable dead-time lead, referenced to VSS. (IR21084 only)
VSS	Logic Ground (21084 only)
V _B	High side floating supply
HO	High side gate driver output
V _S	High side floating supply return
V _{CC}	Low side and logic fixed supply
LO	Low side gate driver output
COM	Low side return

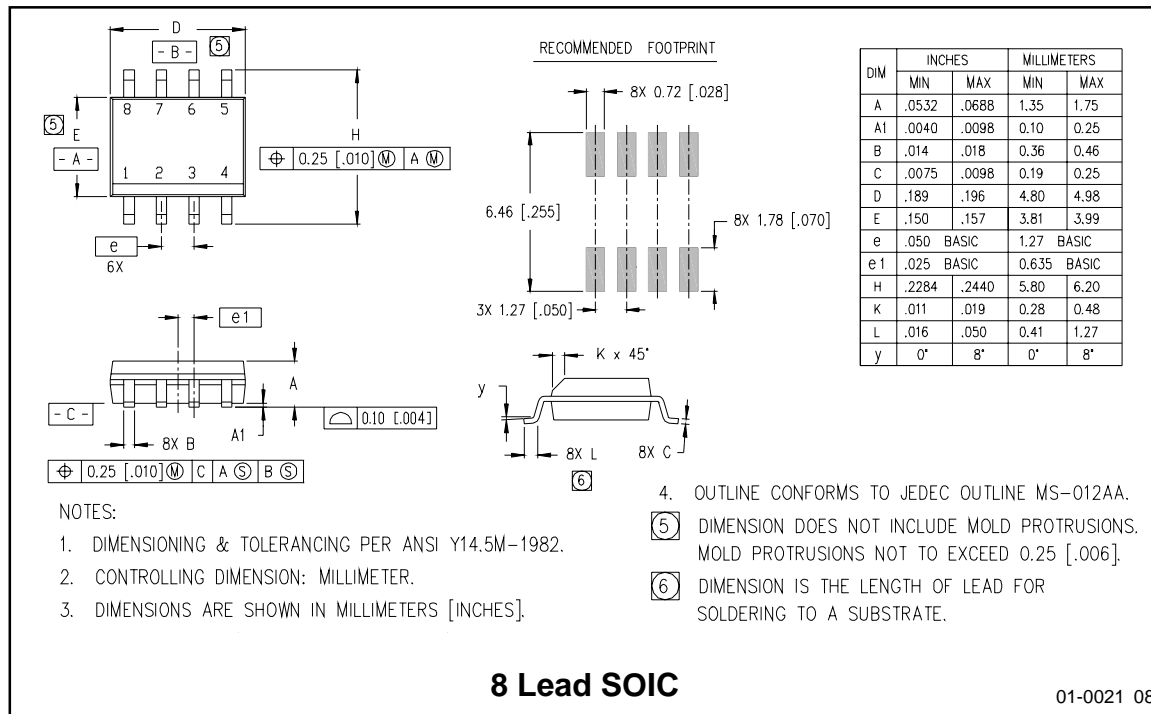
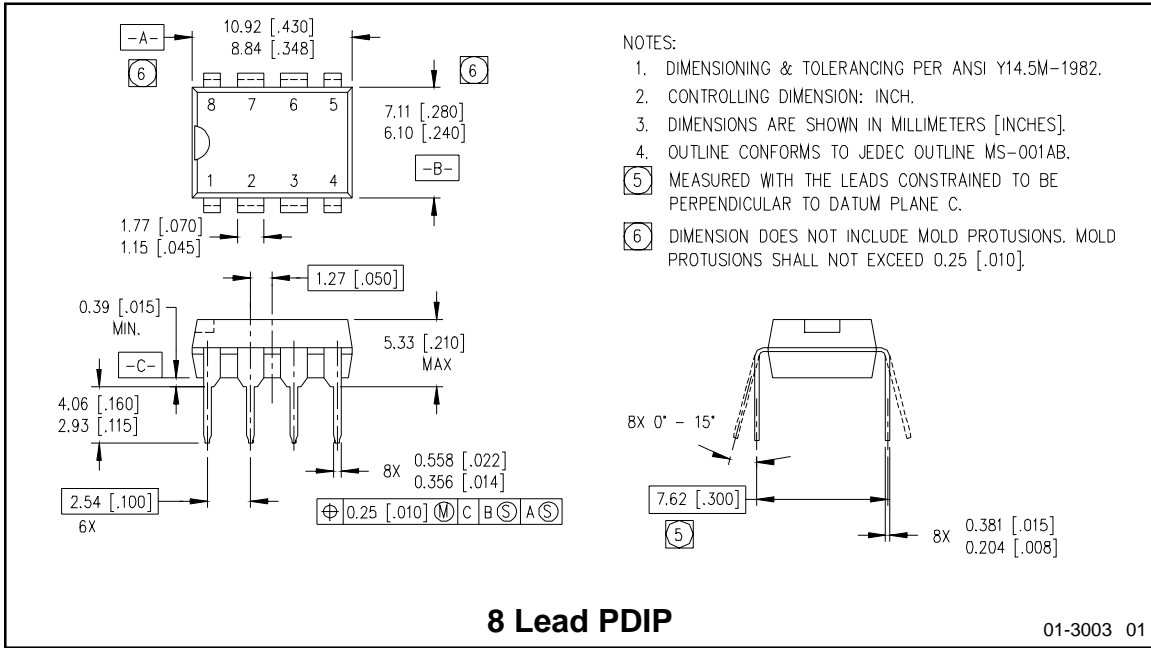
Lead Assignments

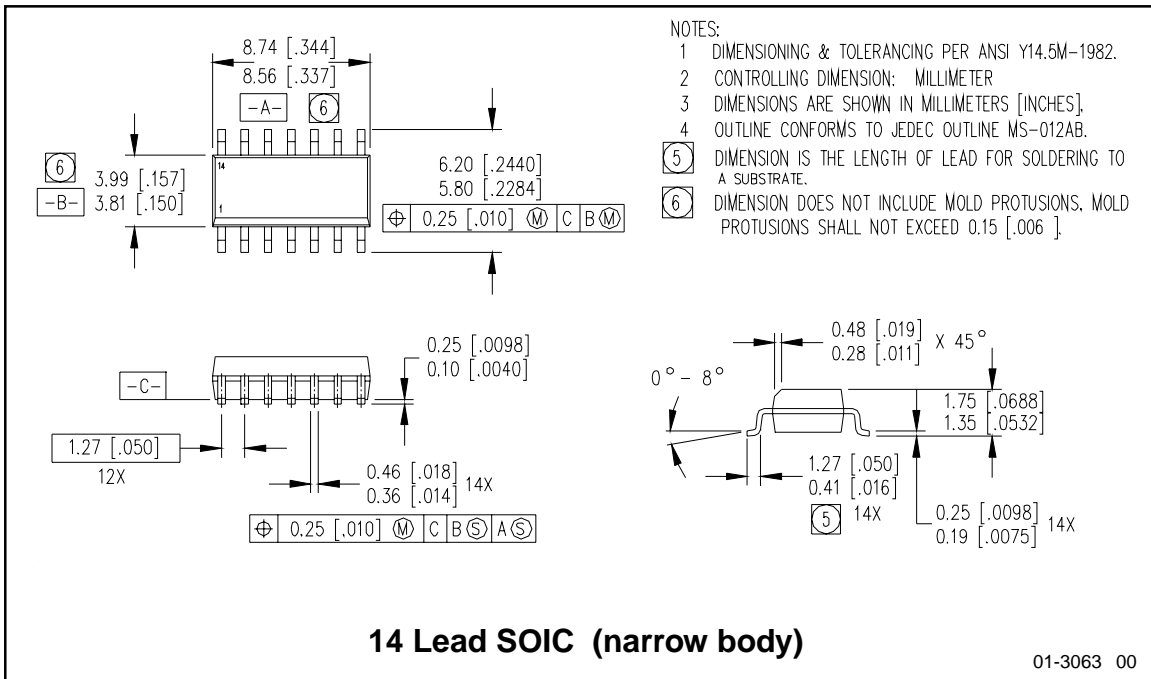
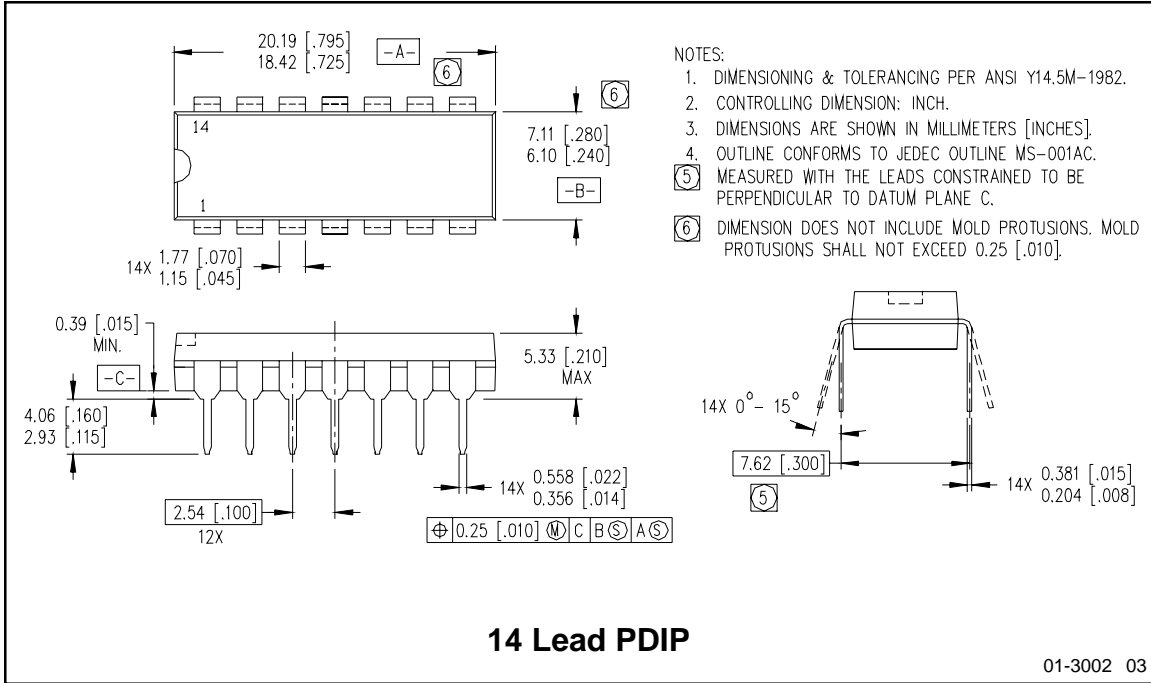
<p>8 Lead PDIP</p>	<p>8 Lead SOIC</p>
IR2108	IR2108S

<p>14 Lead PDIP</p>	<p>14 Lead SOIC</p>
IR21084	IR21084S

IR2108/IR21084 (S)

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IR2108/IR21084 (S)

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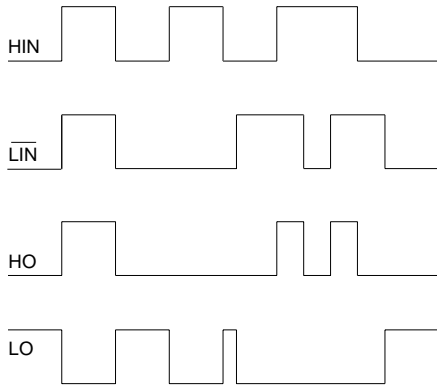


Figure 1. Input/Output Timing Diagram

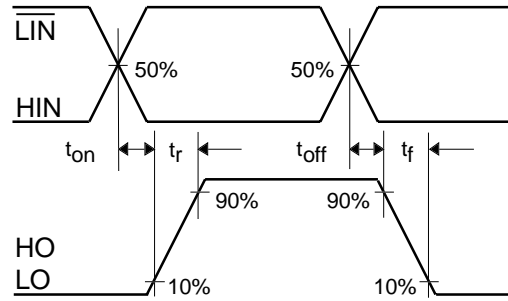


Figure 2. Switching Time Waveform Definitions

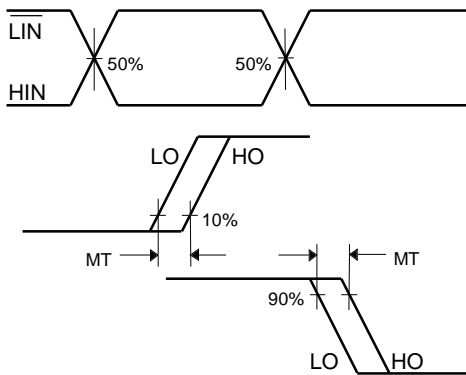


Figure 3. Delay Matching Waveform Definitions

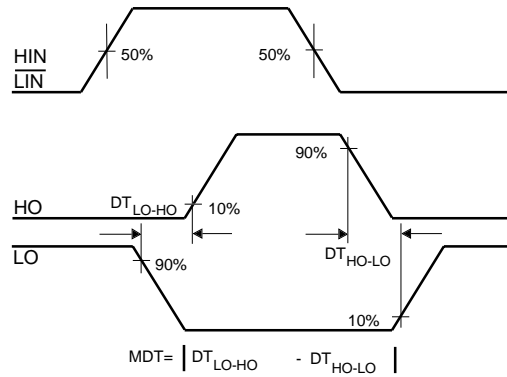


Figure 4. Deadtime Waveform Definitions

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